

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Please cancel claim 21 without prejudice or disclaimer.

Please amend claims 20 and 28 as follows:

1. - 16. (Canceled)

17. (Previously Presented) An apparatus for producing a silicon carbide single crystal where a silicon carbide single crystal substrate that is a seed crystal is disposed inside a container and a source material for the silicon carbide single crystal is supplied to grow the silicon carbide single crystal on the silicon carbide single crystal substrate, the apparatus characterized in that:

a protection layer is formed on a back surface the silicon carbide single crystal substrate;

a supporting part is provided on an inner wall of the container for disposing the silicon carbide single crystal substrate to a predetermined position in the container,

wherein the supporting part supports the silicon carbide single crystal substrate at a periphery of a back surface of the silicon carbide single crystal substrate such that an entire front surface of the silicon carbide single crystal substrate faces the source material to grow the silicon carbide single crystal on a front surface.

18. (Previously Presented) The apparatus for producing a silicon carbide single crystal as in claim 17, further characterized in that:

an opening is formed in a wall of the container at a position facing the protection layer of the silicon carbide single crystal substrate; and

a lid-shaped member is provided so as to close the opening.

19. (Previously Presented) The apparatus for producing a silicon carbide single crystal as in claim 17, further characterized in that:

the protection layer is one of a carbon layer, a layer of carbide with metal having a high melting point, a silicon carbide epitaxial layer, a silicon carbide polycrystalline layer, a silicon carbide amorphous layer and a multilayer film constituted of the above layers.

20. (Currently Amended) An apparatus for producing a silicon carbide single crystal where a silicon carbide single crystal substrate that is a seed crystal is disposed inside a container and a source material for the silicon carbide single crystal is supplied to grow the silicon carbide single crystal on the silicon carbide single crystal substrate, the apparatus characterized in that:

the silicon carbide single crystal substrate having a protection layer on a back surface is disposed so as to close an opening formed in a wall of the container;

the silicon carbide single crystal substrate is supported by a supporting part

disposed on a side wall defining the opening such that an entire front surface of the silicon carbide single crystal substrate faces the source material to grow the silicon carbide single crystal; and

the protection layer is exposed to an outside space.

21. - 23. (Canceled)

24. (Previously Presented) An apparatus for producing a silicon carbide single crystal where a silicon carbide single crystal substrate that is a seed crystal is disposed inside a container and a source material for the silicon carbide single crystal is supplied to grow the silicon carbide single crystal on the silicon carbide single crystal substrate, the apparatus characterized in that:

a protection layer is formed on a back surface the silicon carbide single crystal substrate;

a supporting part is provided on an inner wall of the container for disposing the silicon carbide single crystal substrate to a predetermined position in the container,

wherein the supporting part mechanically supports the silicon carbide single crystal substrate at a periphery of the substrate such that a gap with a predetermined width is provided between the protection layer of the silicon carbide single crystal substrate and an inner wall of the container;

an opening is formed in a wall of the container at a position facing the protection layer of the silicon carbide single crystal substrate; and

a lid-shaped member is provided so as to close the opening and to adjust the predetermined width of the gap.

25. (Previously Presented) The apparatus for producing a silicon carbide single crystal as in claim 17, further characterized in that: a gap with predetermined width is provided between the protection layer of the silicon carbide single crystal substrate and an inner wall of the container.

26. (Previously Presented) The apparatus for producing a silicon carbide single crystal as in claim 17, further characterized in that: the supporting part supports the substrate by being adhered to the substrate with an adhesive.

27. (Previously Presented) The apparatus for producing a silicon carbide single crystal as in claim 20, further characterized in that: the protection layer is a carbon layer that enables a temperature of the silicon carbide single crystal substrate to be monitored from the outside space.

28. (Currently Amended) ~~The apparatus for producing a silicon carbide single crystal as in claim 21, further characterized in that:~~ A substrate for growing a silicon carbide single crystal, comprising:

a silicon carbide single crystal substrate, which is a seed crystal; and

a protection layer formed on a back surface of the silicon carbide single crystal substrate, wherein

a front surface of the silicon carbide single crystal substrate has a supported face supported by a supporting part and disposed at a periphery of the front surface; and
a growth face disposed on a center of the front surface and projecting toward a source material, the growth face for growing the silicon carbide single crystal,
wherein the growth face has a conically shaped inner surface that protrudes from the supported face.